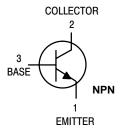
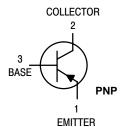


# **Amplifier Transistors**





#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	20	Vdc
Collector–Emitter Voltage	VCES	25	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	5.0	Vdc
Collector Current — Continuous	IC	1.0	Adc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	PD	625 5.0	mW mW/°C
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	1.5 12	Watt mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{ heta JC}$	83.3	°C/W

# BC368 NPN, BC369 PNP

Voltage and current are negative for PNP transistors



CASE 29-04, STYLE 14 TO-92 (TO-226AA)

# BC368 NPN, BC369 PNP

## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic		Min	Тур	Max	Unit
OFF CHARACTERISTICS	<u>.</u>				
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0)	V(BR)CEO	20	_	_	Vdc
Collector–Base Breakdown Voltage ( $I_C = 100 \mu A$ , $I_E = 0$ )	V(BR)CBO	25	_	_	Vdc
Emitter–Base Breakdown Voltage ( $I_E = 100 \mu A, I_C = 0$ )	V(BR)EBO	5.0	_	_	Vdc
Collector Cutoff Current (V <sub>CB</sub> = 25 V, I <sub>E</sub> = 0) (V <sub>CB</sub> = 25 V, I <sub>E</sub> = 0, T <sub>J</sub> = 150°C)	I <sub>CBO</sub>		_	10 1.0	μAdc mAdc
Emitter Cutoff Current (VEB = 5.0 V, I <sub>C</sub> = 0)	I <sub>EBO</sub>	_	_	10	μAdc
ON CHARACTERISTICS	·				
DC Current Gain (V <sub>CE</sub> = 10 V, I <sub>C</sub> = 5.0 mA) (V <sub>CE</sub> = 1.0 V, I <sub>C</sub> = 0.5 A) BC368 (V <sub>CE</sub> = 1.0 V, I <sub>C</sub> = 1.0 A)	h <sub>FE</sub> 3, 369 18–25	50 85 170 60	_ _ _ _	— 375 375 —	_
Bandwidth Product ( $I_C = 10 \text{ mA}$ , $V_{CE} = 5.0 \text{ V}$ , $f = 20 \text{ MHz}$ )	fT	65	_	_	MHz
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 1.0 A, I <sub>B</sub> = 100 mA)		_	_	0.5	V
Base–Emitter On Voltage (I <sub>C</sub> = 1.0 A, V <sub>CE</sub> = 1.0 V)		_	_	1.0	V

## BC368 NPN, BC369 PNP

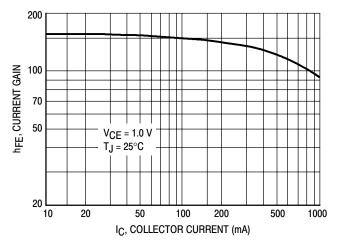


Figure 1. DC Current Gain

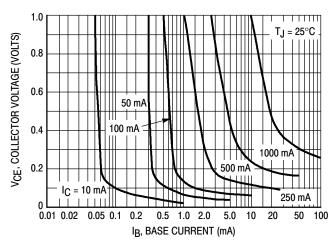


Figure 2. Collector Saturation Region

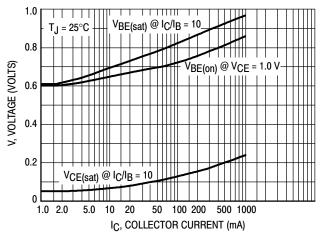
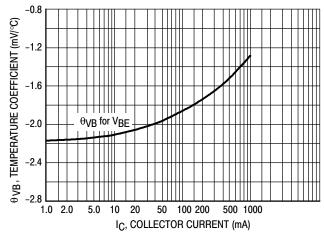


Figure 3. "On" Voltages



**Figure 4. Temperature Coefficient** 

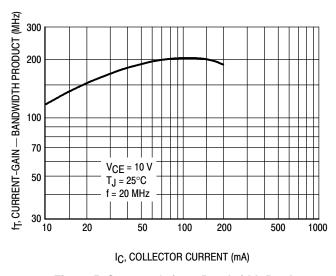


Figure 5. Current-Gain — Bandwidth Product

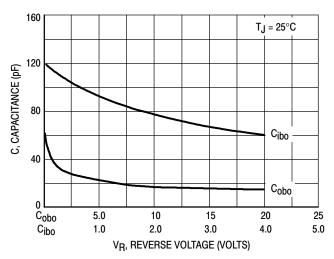
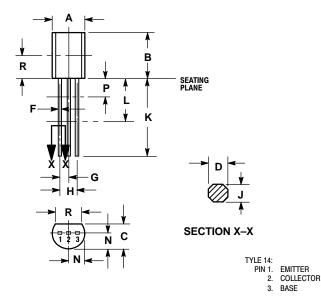


Figure 6. Capacitance

### BC368 NPN, BC369 PNP

#### PACKAGE DIMENSIONS

# CASE 029-04 (TO-226AA) ISSUE AD



#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R
   IS UNCONTROLLED.
- DIMENSION F APPLIES BETWEEN P AND L. DIMENSIONS D AND J APPLY BETWEEN L AND K
  MIMIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION

VIVIIIV	IMUM.				
	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.44	5.21	
В	0.290	0.310	7.37	7.87	
С	0.125	0.165	3.18	4.19	
D	0.018	0.021	0.457	0.533	
F	0.016	0.019	0.407	0.482	
G	0.045	0.055	1.15	1.39	
Н	0.095	0.105	2.42	2.66	
J	0.018	0.024	0.46	0.61	
K	0.500		12.70		
L	0.250		6.35		
N	0.080	0.105	2.04	2.66	
Р		0.100		2.54	
R	0.135		3.43		

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